

2N6605  
2N6606  
2N6607  
2N6608

**SILICON CONTROLLED RECTIFIER  
0.35 AMP, 30 THRU 200 VOLTS**



**TO-18 CASE**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N6605 Series types are hermetically sealed silicon controlled rectifiers manufactured in a TO-18 case, designed for control systems and sensing circuit applications.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_C=25^\circ\text{C}$ )

	SYMBOL	2N6605	2N6606	2N6607	2N6608	UNITS
Peak Repetitive Off-State Voltage	$V_{DRM}, V_{RRM}$	30	60	100	200	V
Average On-State Current	$I_O$		0.35			A
Peak One Cycle Surge Current ( $t=8.3\text{ms}$ )	$I_{TSM}$		6.0			A
Peak Gate Voltage	$V_{GM}$		8.0			V
Operating Junction Temperature	$T_J$		-40 to +125			$^\circ\text{C}$
Storage Temperature	$T_{stg}$		-40 to +150			$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS:** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{DRM}$	Rated $V_{DRM}$ , $R_{GK}=1.0\text{K}\Omega$		120	nA
$I_{RRM}$	Rated $V_{RRM}$		250	nA
$I_{GT}$	$V_D=6.0\text{V}$ , $R_L=100\Omega$		200	$\mu\text{A}$
$V_{GT}$	$V_D=6.0\text{V}$ , $R_L=100\Omega$		0.8	V
$V_{TM}$	$I_T=2.0\text{A}$		2.0	V
$I_H$	$R_{GK}=1.0\text{K}\Omega$		5.0	mA

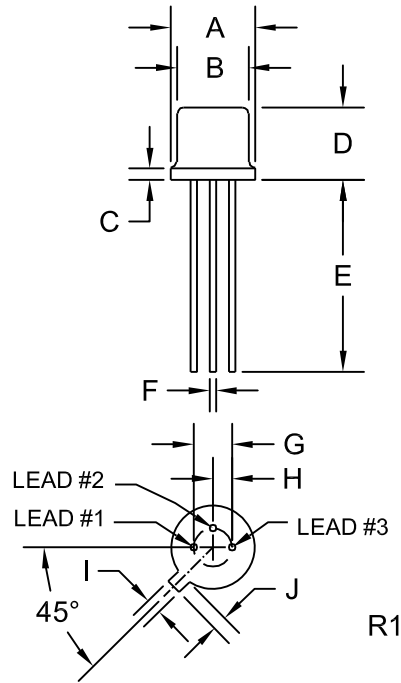
R0 (30-March 2011)

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TO-18 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.209	0.230	5.31	5.84
B (DIA)	0.178	0.195	4.52	4.95
C	-	0.030	-	0.76
D	0.170	0.210	4.32	5.33
E	0.500	-	12.70	-
F (DIA)	0.016	0.019	0.41	0.48
G (DIA)	0.100		2.54	
H	0.050		1.27	
I	0.036	0.046	0.91	1.17
J	0.028	0.048	0.71	1.22

TO-18 (REV: R1)

LEAD CODE:

- 1) Cathode
- 2) Gate
- 3) Anode

MARKING: FULL PART NUMBER

R1

R0 (30-March 2011)